

# Dual Complementary General Purpose Transistor NST3946DP6T5G

The NST3946DP6T5G device is a spin-off of our popular SOT-23/SOT-323/SOT-563 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-963 six-leaded surface mount package. By putting two discrete devices in one package, this device is ideal for low-power surface mount applications where board space is at a premium.

## Features

- $h_{FE}$ , 100–300
- Low  $V_{CE(sat)}$ ,  $\leq 0.4$  V
- Reduces Board Space and Component Count
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	$V_{CEO}$	40	Vdc
Collector – Base Voltage	$V_{CBO}$	60	Vdc
Emitter – Base Voltage	$V_{EBO}$	6.0	Vdc
Collector Current – Continuous	$I_C$	200	mA
Electrostatic Discharge	HBM MM	ESD Class 2 B	

## THERMAL CHARACTERISTICS

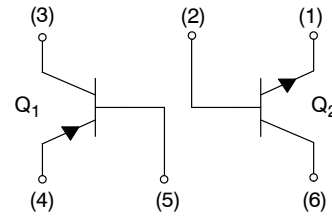
Characteristic (Single Heated)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$ (Note 2)	$P_D$	240 1.9	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	520	$^\circ\text{C/W}$
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$ (Note 3)	$P_D$	280 2.2	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 3)	$R_{\theta JA}$	446	$^\circ\text{C/W}$
Characteristic (Dual Heated) (Note 4)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$ (Note 2)	$P_D$	350 2.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$ (Note 3)	$P_D$	420 3.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 3)	$R_{\theta JA}$	297	$^\circ\text{C/W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air

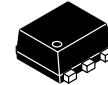
3. FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

4. Dual heated values assume total power is sum of two equally powered channels



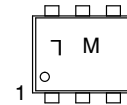
NST3946DP6T5G\*

\*Q1 PNP  
Q2 NPN



SOT-963  
CASE 527AD

## MARKING DIAGRAM



L = Device Code  
(180° Clockwise Rotation)  
M = Date Code

## ORDERING INFORMATION

Device	Package	Shipping†
NST3946DP6T5G	SOT-963 (Pb-Free)	8000 / Tape & Reel

## DISCONTINUED (Note 1)

NSVT3946DP6T5G	SOT-963 (Pb-Free)	8000 / Tape & Reel
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†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

1. **DISCONTINUED:** This device is not recommended for new design. Please contact your onsemi representative for information. The most current information on this device may be available on [www.onsemi.com](http://www.onsemi.com).

# NST3946DP6T5G

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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### OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (Note 5) (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , I <sub>B</sub> = 0) (I <sub>C</sub> = –1.0 mA <sub>dc</sub> , I <sub>B</sub> = 0)	(NPN) (PNP)	V <sub>(BR)CEO</sub>	40 –40	– –	V <sub>dc</sub>
Collector–Base Breakdown Voltage (I <sub>C</sub> = 10 μA <sub>dc</sub> , I <sub>E</sub> = 0) (I <sub>C</sub> = –10 μA <sub>dc</sub> , I <sub>E</sub> = 0)	(NPN) (PNP)	V <sub>(BR)CBO</sub>	60 –40	– –	V <sub>dc</sub>
Emitter–Base Breakdown Voltage (I <sub>E</sub> = 10 μA <sub>dc</sub> , I <sub>C</sub> = 0) (I <sub>E</sub> = –10 μA <sub>dc</sub> , I <sub>C</sub> = 0)	(NPN) (PNP)	V <sub>(BR)EBO</sub>	6.0 –5.0	– –	V <sub>dc</sub>
Collector Cutoff Current (V <sub>CE</sub> = 30 V <sub>dc</sub> , V <sub>EB</sub> = 3.0 V <sub>dc</sub> ) (V <sub>CE</sub> = –30 V <sub>dc</sub> , V <sub>EB</sub> = –3.0 V <sub>dc</sub> )	(NPN) (PNP)	I <sub>CEX</sub>	– –	50 –50	nA <sub>dc</sub>

### ON CHARACTERISTICS (Note 5)

DC Current Gain (I <sub>C</sub> = 0.1 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 V <sub>dc</sub> ) (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 V <sub>dc</sub> ) (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 V <sub>dc</sub> ) (I <sub>C</sub> = 50 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 V <sub>dc</sub> ) (I <sub>C</sub> = 100 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 V <sub>dc</sub> )  (I <sub>C</sub> = –0.1 mA <sub>dc</sub> , V <sub>CE</sub> = –1.0 V <sub>dc</sub> ) (I <sub>C</sub> = –1.0 mA <sub>dc</sub> , V <sub>CE</sub> = –1.0 V <sub>dc</sub> ) (I <sub>C</sub> = –10 mA <sub>dc</sub> , V <sub>CE</sub> = –1.0 V <sub>dc</sub> ) (I <sub>C</sub> = –50 mA <sub>dc</sub> , V <sub>CE</sub> = –1.0 V <sub>dc</sub> ) (I <sub>C</sub> = –100 mA <sub>dc</sub> , V <sub>CE</sub> = –1.0 V <sub>dc</sub> )	(NPN)      (PNP)	h <sub>FE</sub>	40 70 100 60 30  60 80 100 60 30	– – 300 – –  – – 300 – –	–
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 10 mA <sub>dc</sub> , I <sub>B</sub> = 1.0 mA <sub>dc</sub> ) (I <sub>C</sub> = 50 mA <sub>dc</sub> , I <sub>B</sub> = 5.0 mA <sub>dc</sub> )  (I <sub>C</sub> = –10 mA <sub>dc</sub> , I <sub>B</sub> = –1.0 mA <sub>dc</sub> ) (I <sub>C</sub> = –50 mA <sub>dc</sub> , I <sub>B</sub> = –5.0 mA <sub>dc</sub> )	(NPN)   (PNP)	V <sub>CE(sat)</sub>	– –  – –	0.2 0.3  –0.25 –0.4	V <sub>dc</sub>
Base–Emitter Saturation Voltage (I <sub>C</sub> = 10 mA <sub>dc</sub> , I <sub>B</sub> = 1.0 mA <sub>dc</sub> ) (I <sub>C</sub> = 50 mA <sub>dc</sub> , I <sub>B</sub> = 5.0 mA <sub>dc</sub> )  (I <sub>C</sub> = –10 mA <sub>dc</sub> , I <sub>B</sub> = –1.0 mA <sub>dc</sub> ) (I <sub>C</sub> = –50 mA <sub>dc</sub> , I <sub>B</sub> = –5.0 mA <sub>dc</sub> )	(NPN)   (PNP)	V <sub>BE(sat)</sub>	0.65 –  –0.65 –	0.85 0.95  –0.85 –0.95	V <sub>dc</sub>

5. Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2.0%.

# NST3946DP6T5G

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
<b>SMALL-SIGNAL CHARACTERISTICS</b>				
Current-Gain-Bandwidth Product ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 20\text{ Vdc}$ , $f = 100\text{ MHz}$ ) (NPN) ( $I_C = -10\text{ mAdc}$ , $V_{CE} = -20\text{ Vdc}$ , $f = 100\text{ MHz}$ ) (PNP)	$f_T$	200 250	– –	MHz
Output Capacitance ( $V_{CB} = 5.0\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ ) (NPN) ( $V_{CB} = -5.0\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ ) (PNP)	$C_{obo}$	– –	4.0 4.5	pF
Input Capacitance ( $V_{EB} = 0.5\text{ Vdc}$ , $I_C = 0$ , $f = 1.0\text{ MHz}$ ) (NPN) ( $V_{EB} = -0.5\text{ Vdc}$ , $I_C = 0$ , $f = 1.0\text{ MHz}$ ) (PNP)	$C_{ibo}$	– –	8.0 10.0	pF
Noise Figure ( $V_{CE} = 5.0\text{ Vdc}$ , $I_C = 100\text{ }\mu\text{Adc}$ , $R_S = 1.0\text{ k }\Omega$ , $f = 1.0\text{ kHz}$ ) (NPN) ( $V_{CE} = -5.0\text{ Vdc}$ , $I_C = -100\text{ }\mu\text{Adc}$ , $R_S = 1.0\text{ k }\Omega$ , $f = 1.0\text{ kHz}$ ) (PNP)	NF	– –	5.0 4.0	dB

## SWITCHING CHARACTERISTICS

Delay Time	( $V_{CC} = 3.0\text{ Vdc}$ , $V_{BE} = -0.5\text{ Vdc}$ ) (NPN) ( $V_{CC} = -3.0\text{ Vdc}$ , $V_{BE} = 0.5\text{ Vdc}$ ) (PNP)	$t_d$	– –	35 35	ns
Rise Time	( $I_C = 10\text{ mAdc}$ , $I_{B1} = 1.0\text{ mAdc}$ ) (NPN) ( $I_C = -10\text{ mAdc}$ , $I_{B1} = -1.0\text{ mAdc}$ ) (PNP)	$t_r$	– –	35 35	
Storage Time	( $V_{CC} = 3.0\text{ Vdc}$ , $I_C = 10\text{ mAdc}$ ) (NPN) ( $V_{CC} = -3.0\text{ Vdc}$ , $I_C = -10\text{ mAdc}$ ) (PNP)	$t_s$	– –	275 250	ns
Fall Time	( $I_{B1} = I_{B2} = 1.0\text{ mAdc}$ ) (NPN) ( $I_{B1} = I_{B2} = -1.0\text{ mAdc}$ ) (PNP)	$t_f$	– –	50 50	

## NPN TRANSISTOR

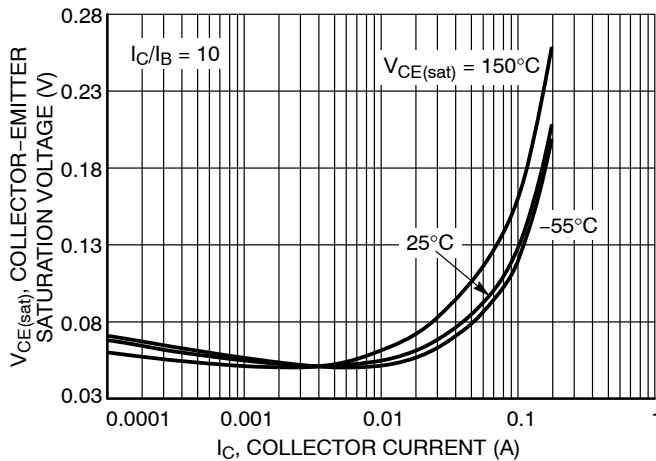


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

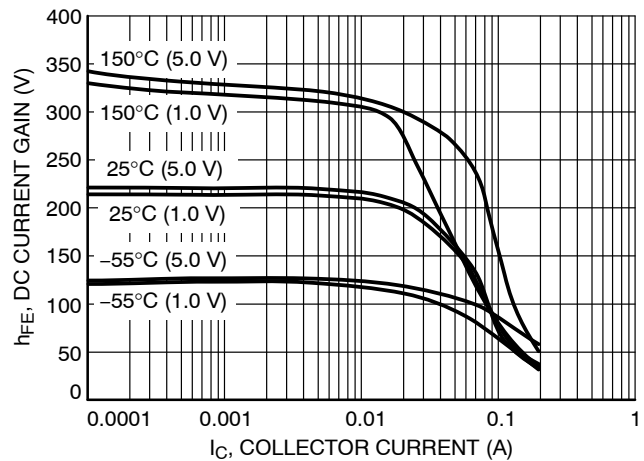
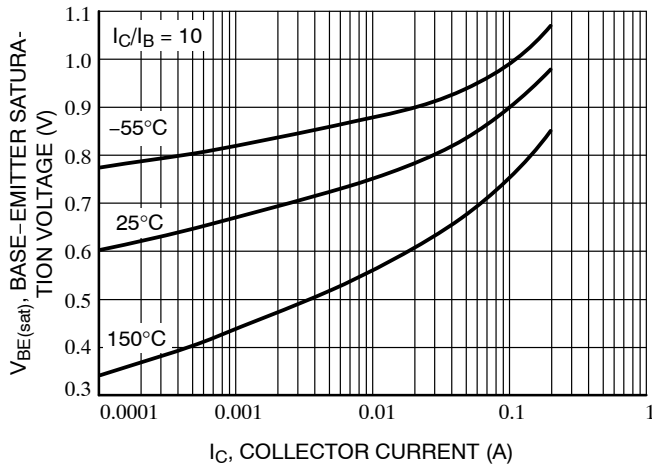


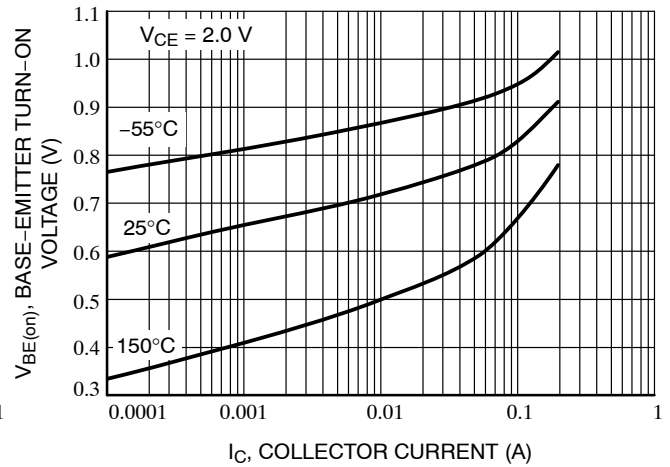
Figure 2. DC Current Gain vs. Collector Current

# NST3946DP6T5G

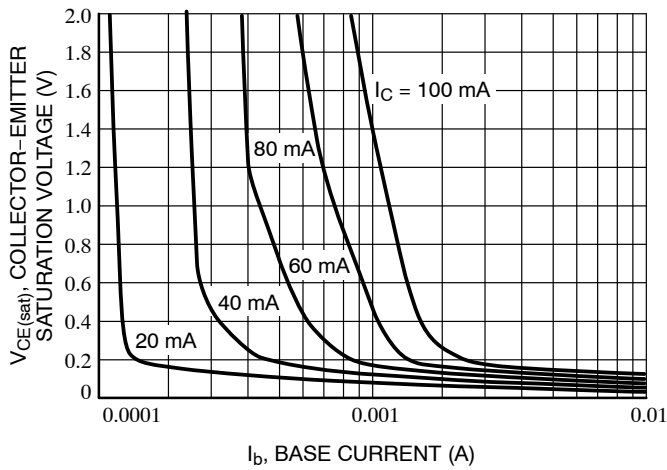
## NPN TRANSISTOR



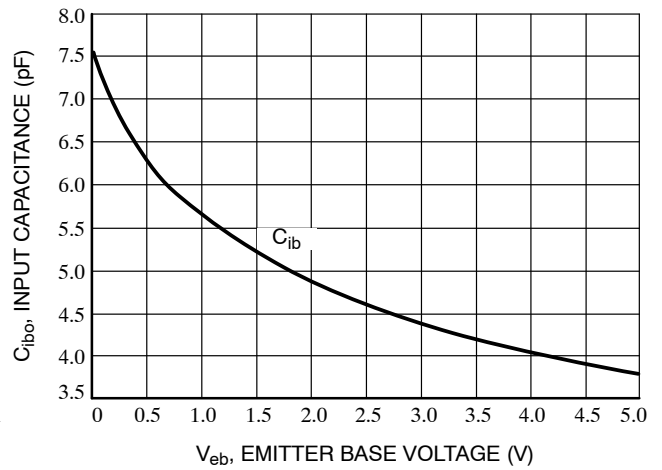
**Figure 3. Base Emitter Saturation Voltage vs. Collector Current**



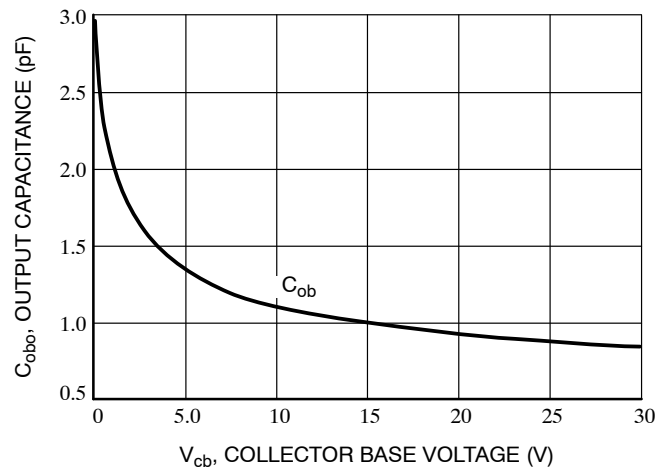
**Figure 4. Base Emitter Turn-On Voltage vs. Collector Current**



**Figure 5. Saturation Region**



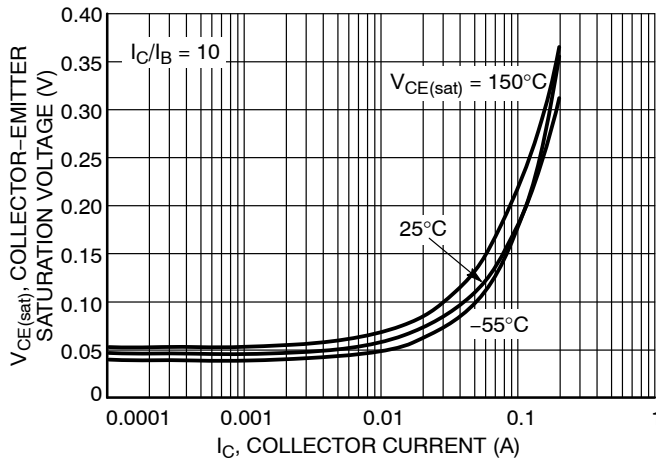
**Figure 6. Input Capacitance**



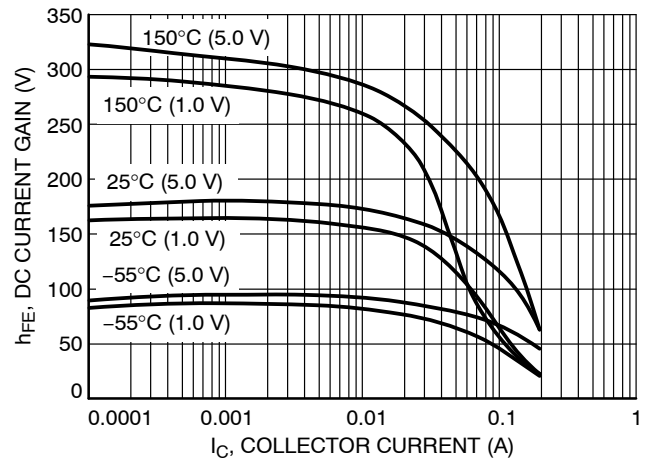
**Figure 7. Output Capacitance**

# NST3946DP6T5G

## PNP TRANSISTOR



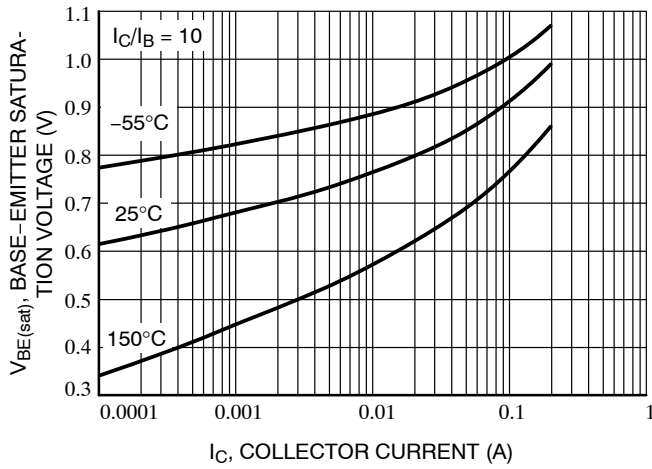
**Figure 8. Collector Emitter Saturation Voltage vs. Collector Current**



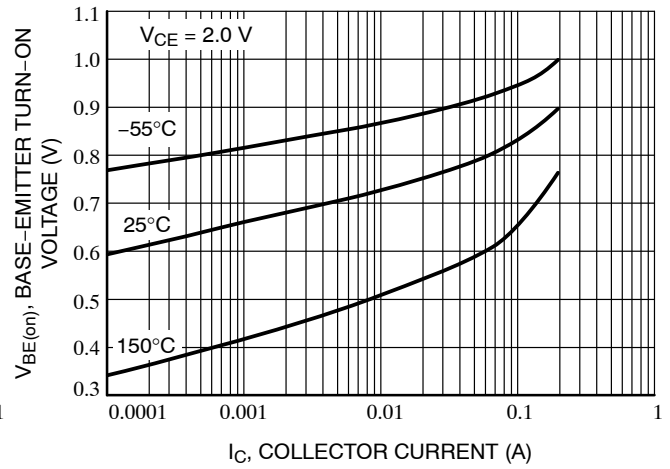
**Figure 9. DC Current Gain vs. Collector Current**

# NST3946DP6T5G

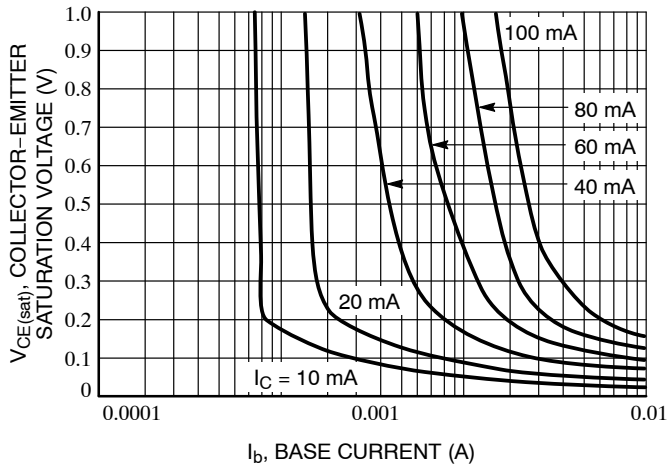
## PNP TRANSISTOR



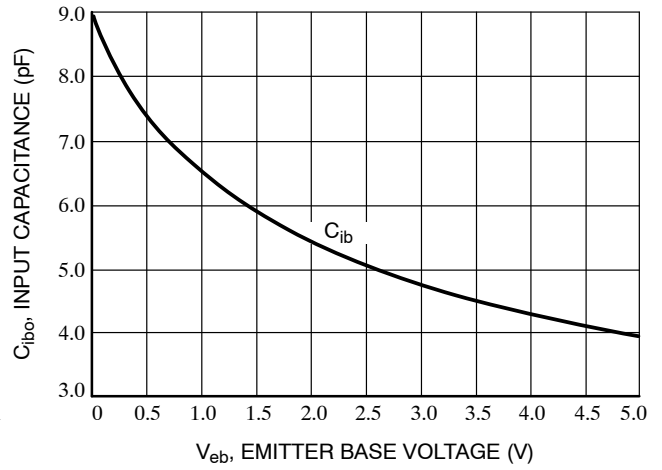
**Figure 10. Base Emitter Saturation Voltage vs. Collector Current**



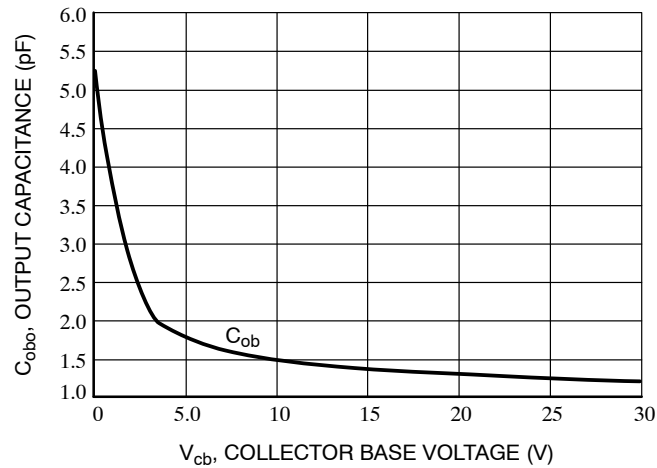
**Figure 11. Base Emitter Turn-On Voltage vs. Collector Current**



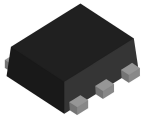
**Figure 12. Saturation Region**



**Figure 13. Input Capacitance**



**Figure 14. Output Capacitance**

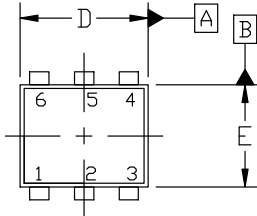


**SOT-963 1.00x1.00x0.37, 0.35P**  
**CASE 527AD**  
**ISSUE F**

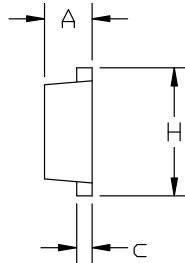
DATE 20 FEB 2024

NOTES:

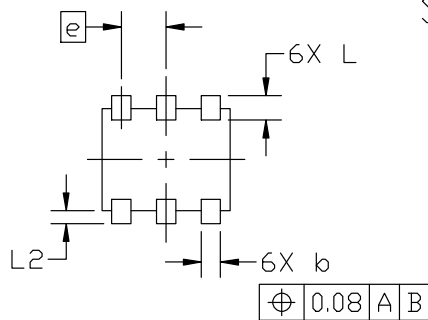
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.



TOP VIEW

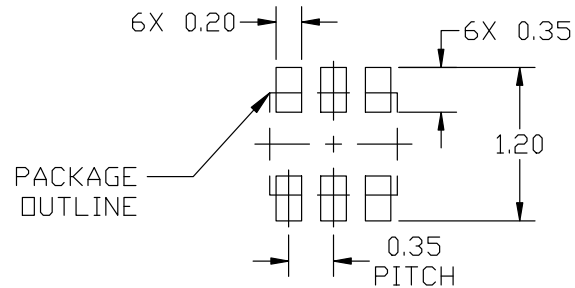


SIDE VIEW



BOTTOM VIEW

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.34	0.37	0.40
b	0.10	0.15	0.20
c	0.07	0.12	0.17
D	0.95	1.00	1.05
E	0.75	0.80	0.85
e	0.35 BSC		
H	0.95	1.00	1.05
L	0.19 REF		
L2	0.05	0.10	0.15



RECOMMENDED MOUNTING  
FOOTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERRM/D.

STYLE 1:

- PIN 1. EMITTER 1  
2. BASE 1  
3. COLLECTOR 2  
4. EMITTER 2  
5. BASE 2  
6. COLLECTOR 1

STYLE 2:

- PIN 1. EMITTER 1  
2. EMITTER 2  
3. BASE 2  
4. COLLECTOR 2  
5. BASE 1  
6. COLLECTOR 1

STYLE 3:

- PIN 1. CATHODE 1  
2. CATHODE 1  
3. ANODE/ANODE 2  
4. CATHODE 2  
5. CATHODE 2  
6. ANODE/ANODE 1

STYLE 4:

- PIN 1. COLLECTOR  
2. COLLECTOR  
3. BASE  
4. EMITTER  
5. COLLECTOR  
6. COLLECTOR

STYLE 5:

- PIN 1. CATHODE  
2. CATHODE  
3. ANODE  
4. ANODE  
5. CATHODE  
6. CATHODE

STYLE 6:

- PIN 1. CATHODE  
2. ANODE  
3. CATHODE  
4. CATHODE  
5. CATHODE  
6. CATHODE

STYLE 7:

- PIN 1. CATHODE  
2. ANODE  
3. CATHODE  
4. CATHODE  
5. ANODE  
6. CATHODE

STYLE 8:

- PIN 1. DRAIN  
2. DRAIN  
3. GATE  
4. SOURCE  
5. DRAIN  
6. DRAIN

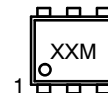
STYLE 9:

- PIN 1. SOURCE 1  
2. GATE 1  
3. DRAIN 2  
4. SOURCE 2  
5. GATE 2  
6. DRAIN 1

STYLE 10:

- PIN 1. CATHODE 1  
2. N/C  
3. CATHODE 2  
4. ANODE 2  
5. N/C  
6. ANODE 1

**GENERIC  
MARKING DIAGRAM\***



XX = Specific Device Code  
M = Month Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

<b>DOCUMENT NUMBER:</b>	<b>98AON26456D</b>	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
<b>DESCRIPTION:</b>	<b>SOT-963 1.00x1.00x0.37, 0.35P</b>	<b>PAGE 1 OF 1</b>

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